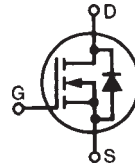


Polar™
Power MOSFET

IXTA05N100P
IXTP05N100P

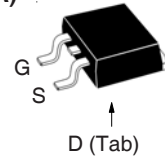
$V_{DSS} = 1000V$
 $I_{D25} = 0.5A$
 $R_{DS(on)} \leq 30\Omega$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

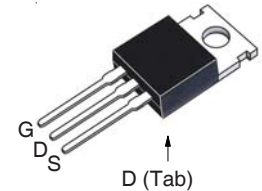


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	1000	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	0.5	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	1.25	A
I_A	$T_C = 25^\circ C$	0.5	A
E_{AS}	$T_C = 25^\circ C$	50	mJ
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	10	V/ns
P_D	$T_C = 25^\circ C$	50	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
F_C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in
Weight	TO-263	2.5	g
	TO-220	3.0	g

TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
S = Source Tab = Drain

Features

- International Standard Packages
- Avalanche Rated
- Fast Intrinsic Diode
- Dynamic dv/dt Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 50\mu A$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 50 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$			10 μA 750 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1		24	30 Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 30\text{V}, I_D = 0.5 \cdot I_{D25}$, Note 1	0.24	0.40	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		196	pF
C_{oss}			15	pF
C_{rss}			4	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 50\text{V}, I_D = 0.5 \cdot I_{D25}$ $R_G = 30\Omega$ (External)		6	ns
t_r			15	ns
$t_{d(off)}$			20	ns
t_f			15	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		8.1	nC
Q_{gs}			0.7	nC
Q_{gd}			4.2	nC
R_{thJC}				2.5 $^\circ\text{C/W}$
R_{thCS}	TO-220		0.50	$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			0.5 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			2.0 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}$, Note 1			1.2 V
t_{rr}	$I_F = 0.5\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$		750	ns

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

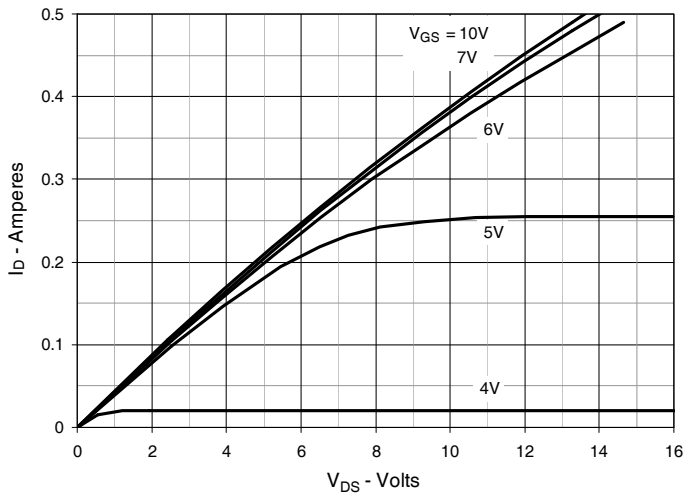


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

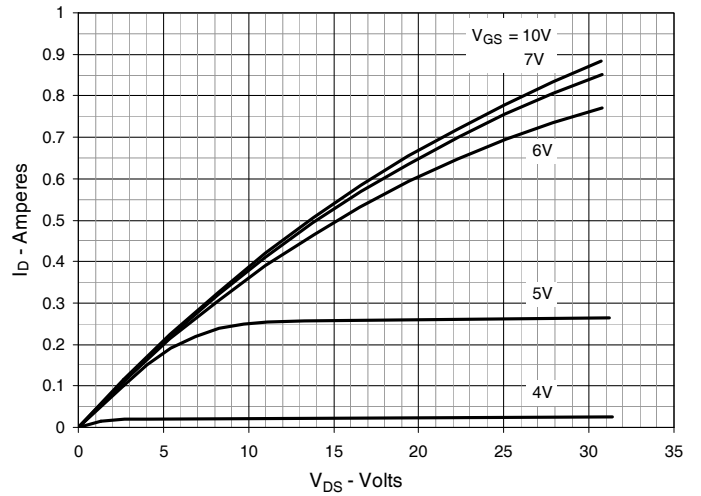


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

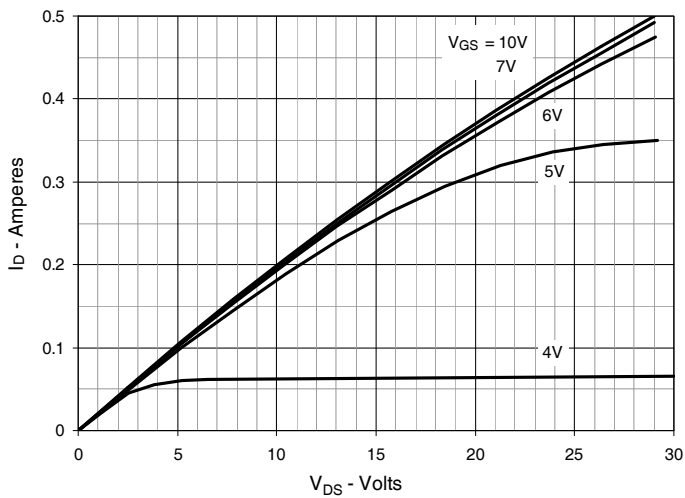


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 0.25\text{A}$ Value vs. Junction Temperature

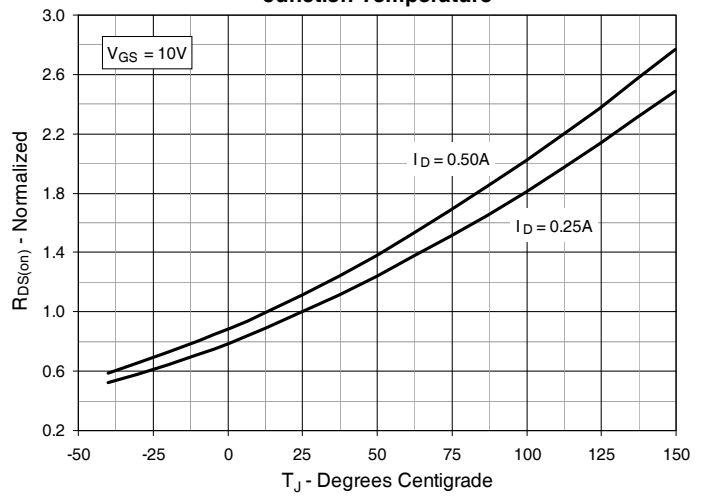


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 0.25\text{A}$ Value vs. Drain Current

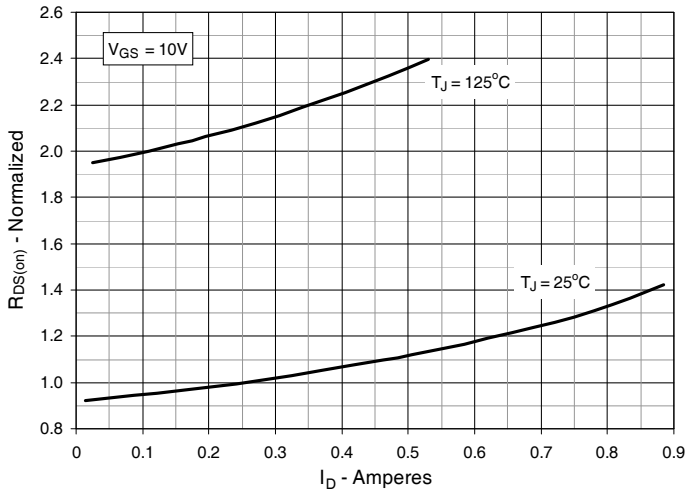


Fig. 6. Maximum Drain Current vs. Case Temperature

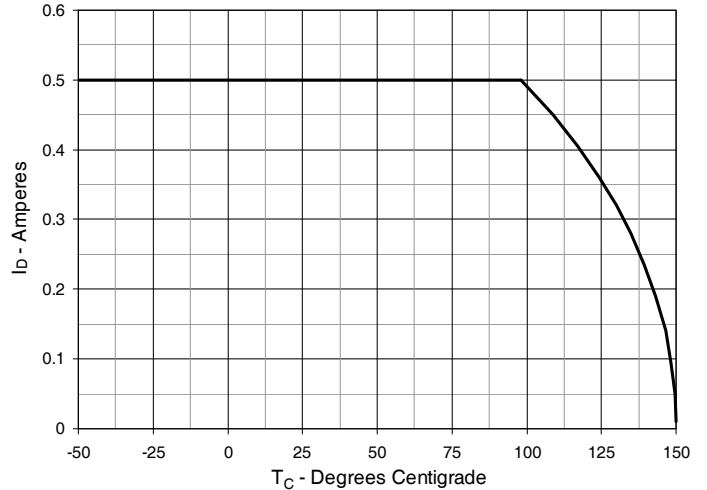


Fig. 7. Input Admittance

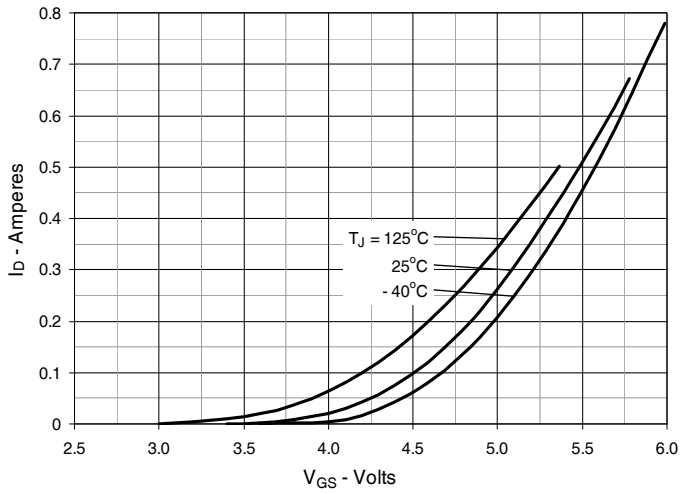


Fig. 8. Transconductance

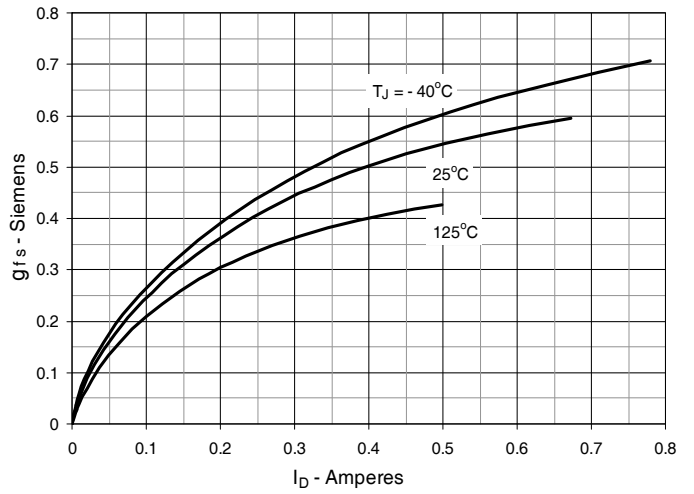


Fig. 9. Forward Voltage Drop of Intrinsic Diode

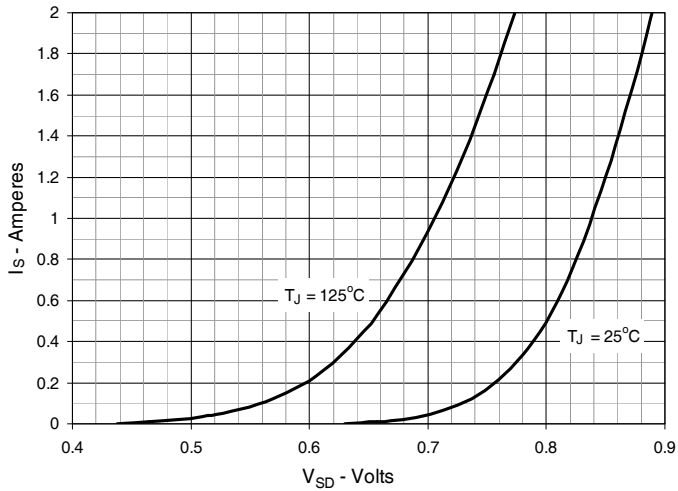


Fig. 10. Gate Charge

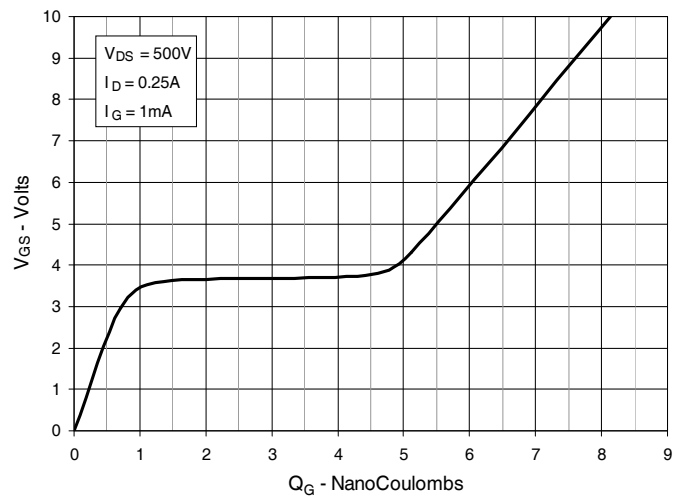


Fig. 11. Capacitance

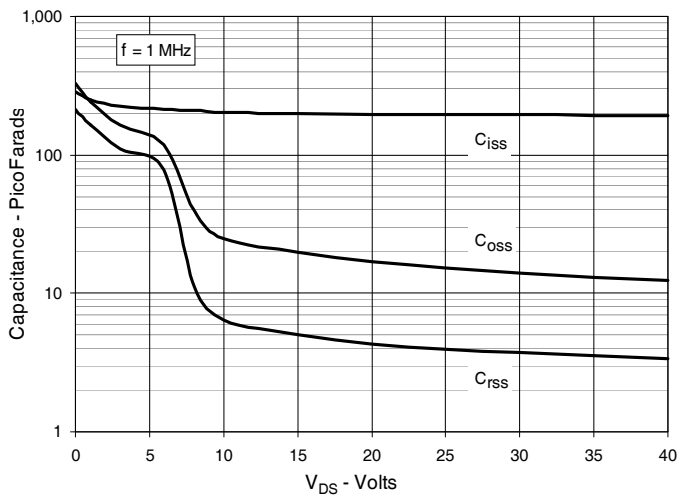


Fig. 12. Forward-Bias Safe Operating Area

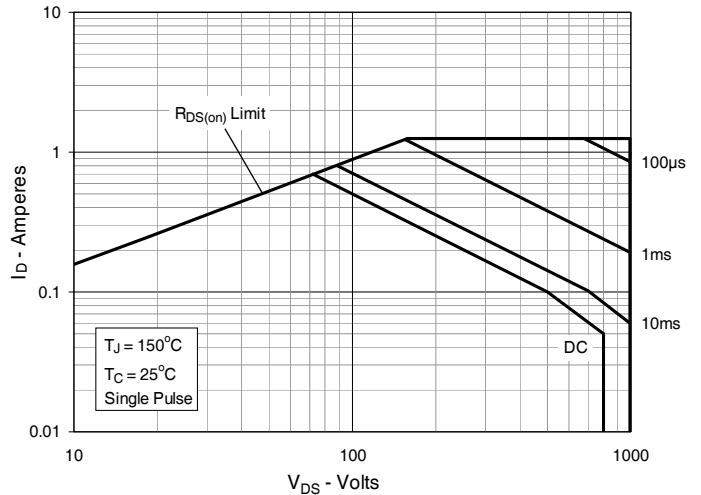
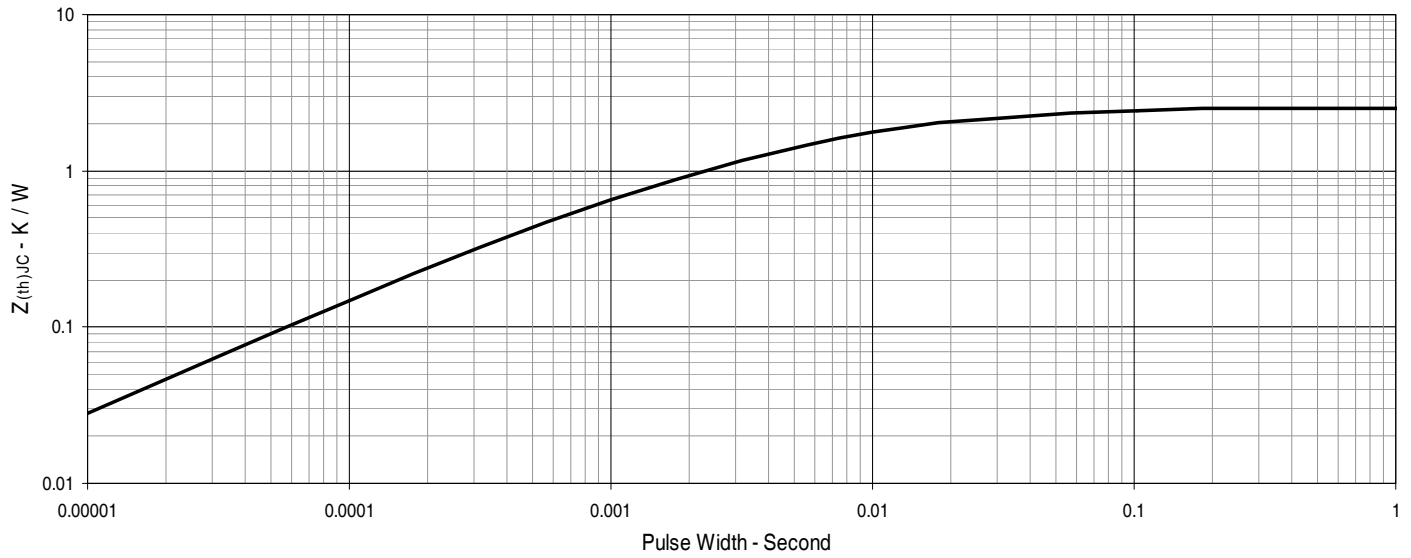
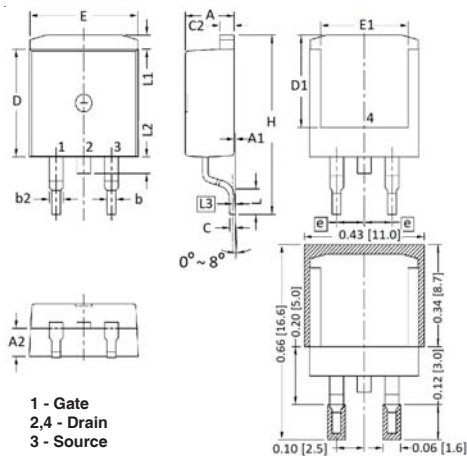


Fig. 13. Maximum Transient Thermal Impedance

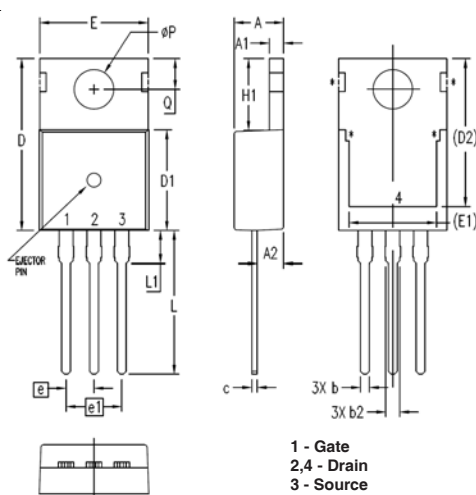


TO-263 Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.060	1.18	1.52
C	.018	.024	0.45	0.60
C2	.049	.060	1.25	1.52
D	.340	.370	8.63	9.40
D1	.300	.327	7.62	8.30
E	.380	.410	9.65	10.41
E1	.270	.330	6.86	8.38
e	.100 BSC		2.54 BSC	
H	.580	.620	14.73	15.75
L	.075	.105	1.91	2.67
L1	.039	.060	1.00	1.52
L2	—	.070	—	1.77
L3	.010 BSC		0.254 BSC	

TO-220 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100 BSC		2.54 BSC	
e1	.200 BSC		5.08 BSC	
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
ØP	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20



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